Ordering number : EN2679A

SANYO

No.2679A

2SC4291

NPN Triple Diffused Planar Silicon Transistor

Ultrahigh-Definition Color Display Horizontal Deflection Output Applications

Features

- High speed (t_f = 0.3 μs max).
- High breakdown voltage (V_{CBO} = 1500V).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- On-chip damper diode.

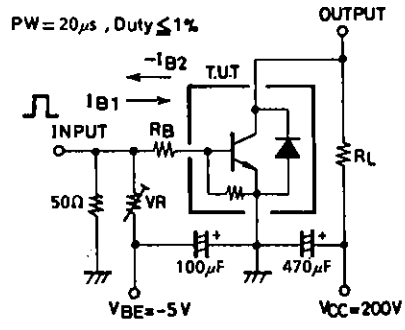
Absolute Maximum Ratings at Ta = 25°C

				unit
Collector-to-Base Voltage	V_{CBO}		1500	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		5	A
Collector Current (Pulse)	I_{CP}		16	A
Collector Dissipation	P_C		2.5	W
		Tc = 25°C	100	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta = 25°C

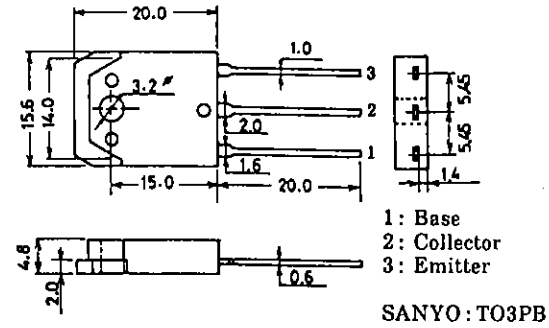
			min	typ	max	unit
Collector Cutoff Current	I_{CES}	V_{CE} = 1500V			1.0	mA
Collector Cutoff Current	I_{CBO}	V_{CB} = 800V, I_E = 0			10	μA
Collector Sustain Voltage	$V_{CEO(sus)}$	I_C = 100mA, I_B = 0	800			V
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	40		130	mA
C-E Saturation Voltage	$V_{CE(sat)}$	I_C = 4A, I_B = 1A			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C = 4A, I_B = 1A			1.5	V
DC Current Gain	$h_{FE}(1)$	V_{CE} = 5V, I_C = 1A	8			
	$h_{FE}(2)$	V_{CE} = 5V, I_C = 4A	4		6	
Diode Forward Voltage	V_F	I_{EC} = 5A, I_B = 0			2.0	V
Storage Time	t_{stg}	I_C = 4A, I_{B1} = 0.8A, I_{B2} = −1.6A			3.0	μs
Fall Time	t_f	I_C = 4A, I_{B1} = 0.8A, I_{B2} = −1.6A			0.3	μs

Switching Time Test Circuit



Package Dimensions 2022A

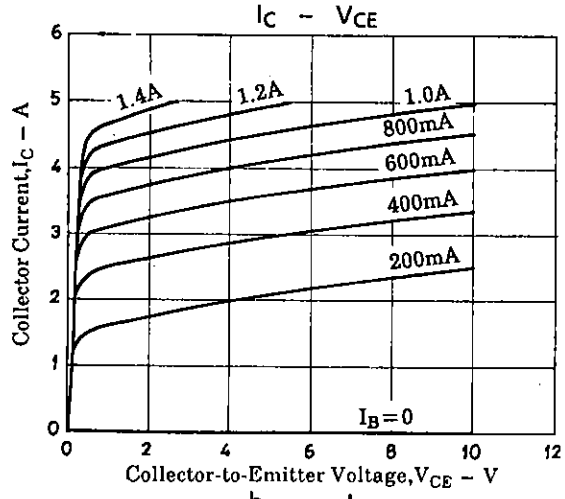
(unit : mm)



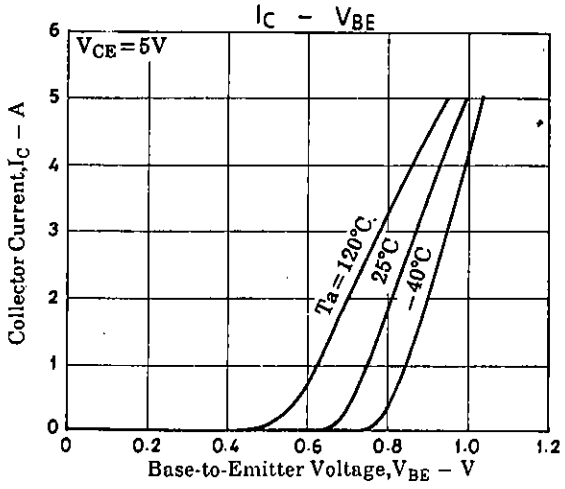
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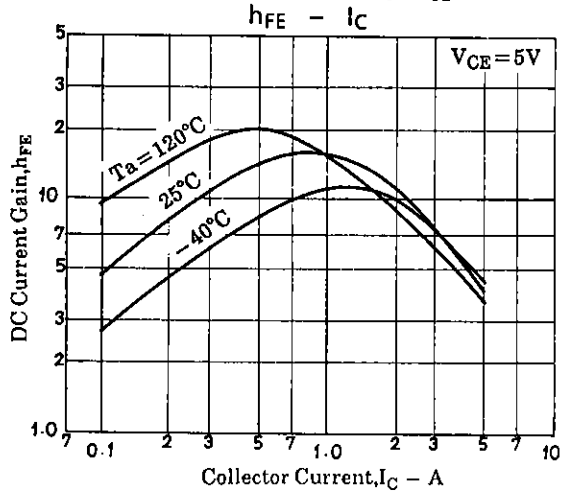
I_C – V_{CE}



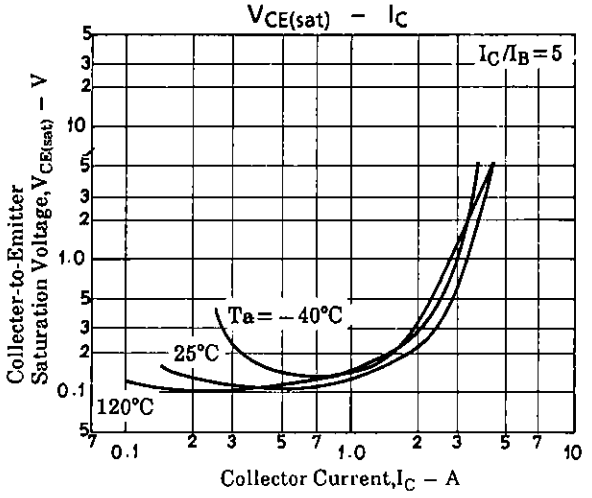
I_C – V_{BE}



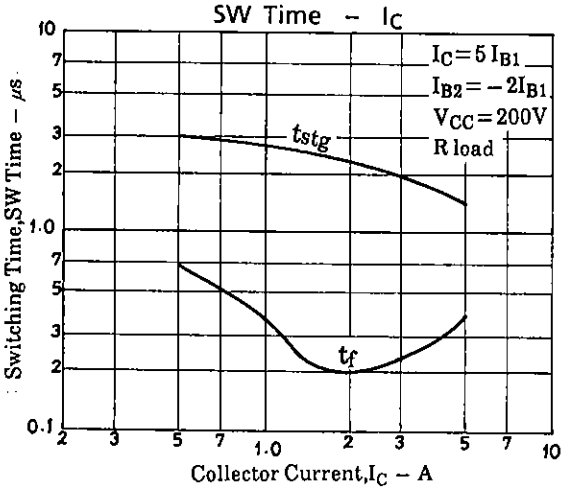
h_{FE} – I_C



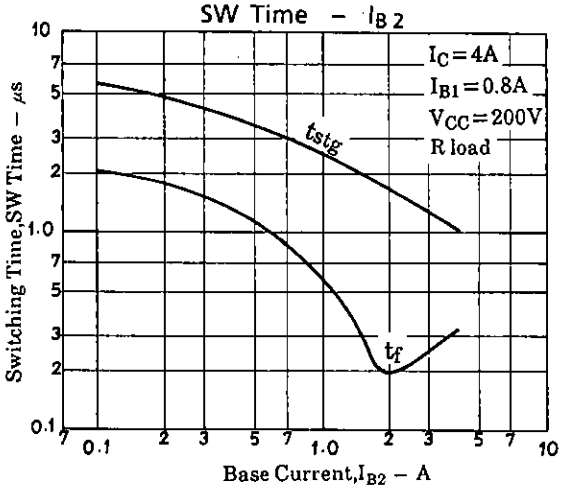
$V_{CE(sat)}$ – I_C



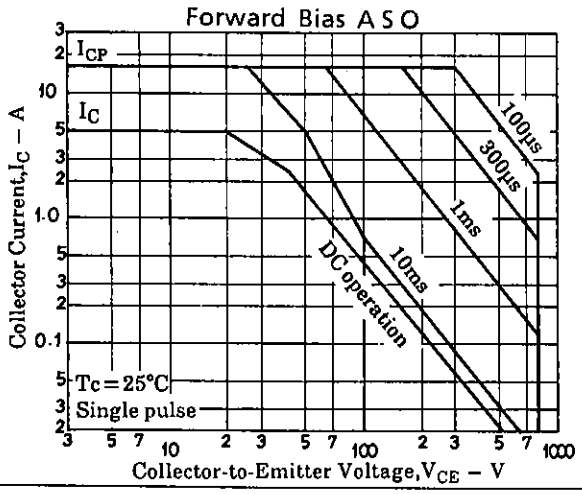
SW Time – I_C



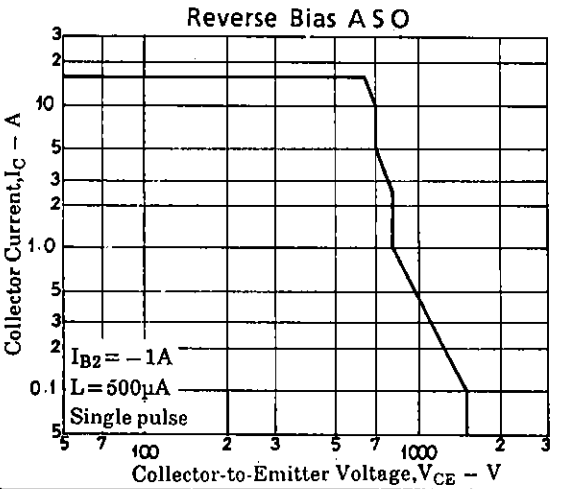
SW Time – I_{B2}

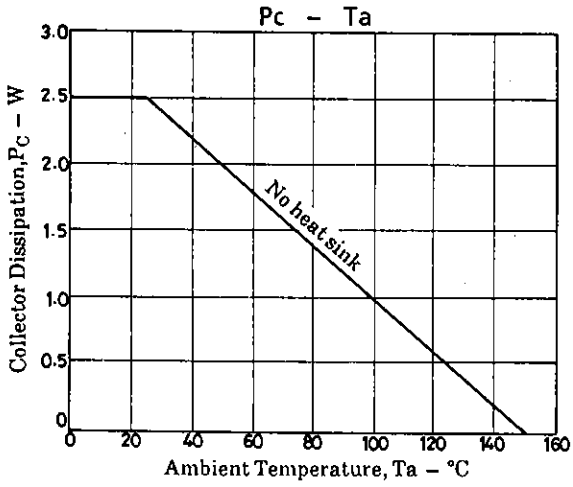


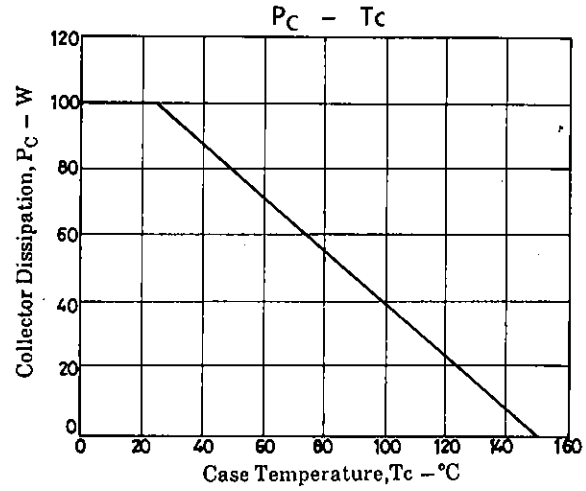
Forward Bias A S O



Reverse Bias A S O







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